

FIG. 1

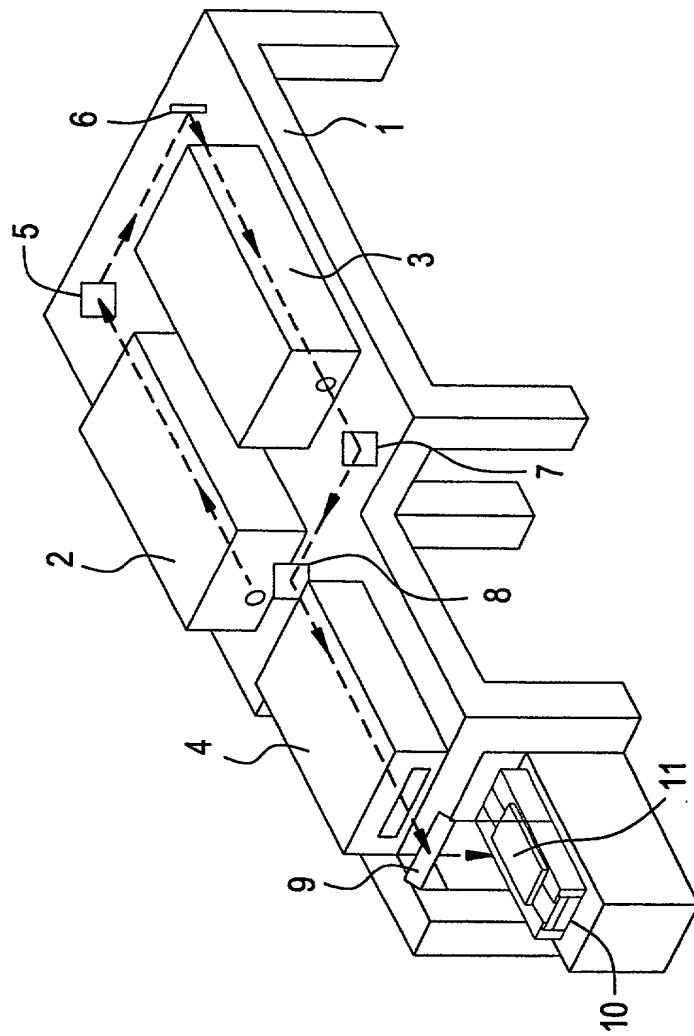


FIG. 2

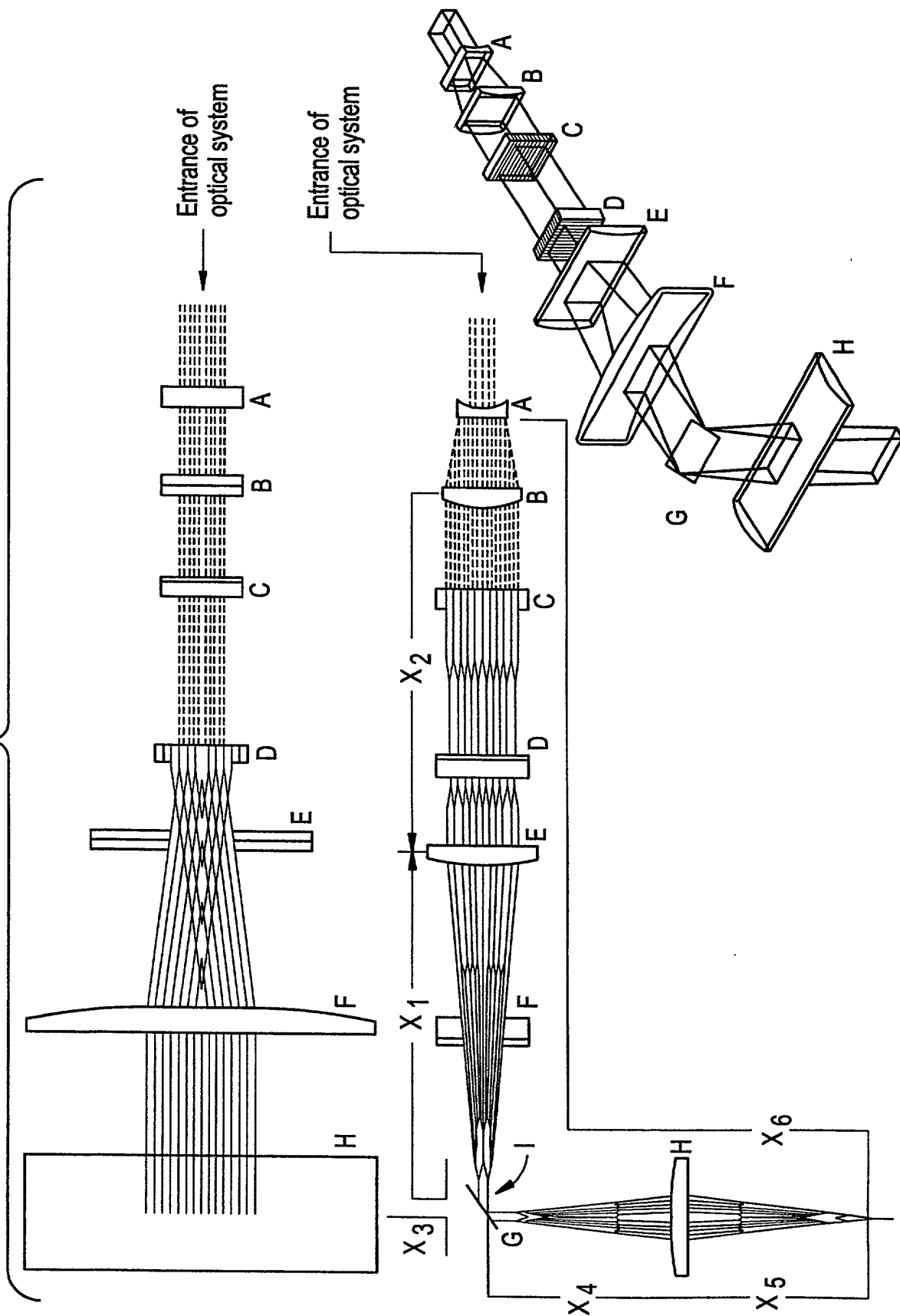


FIG. 3
PRIOR ART

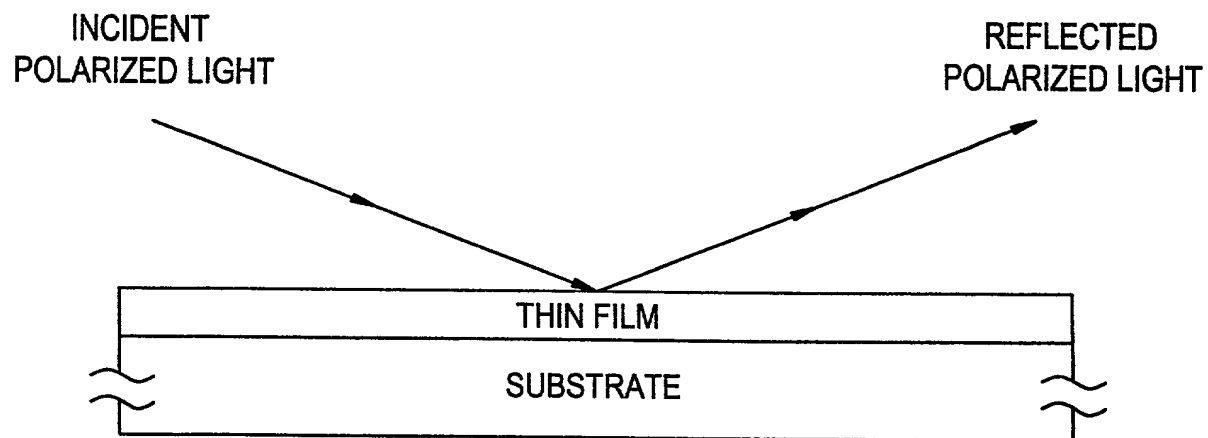
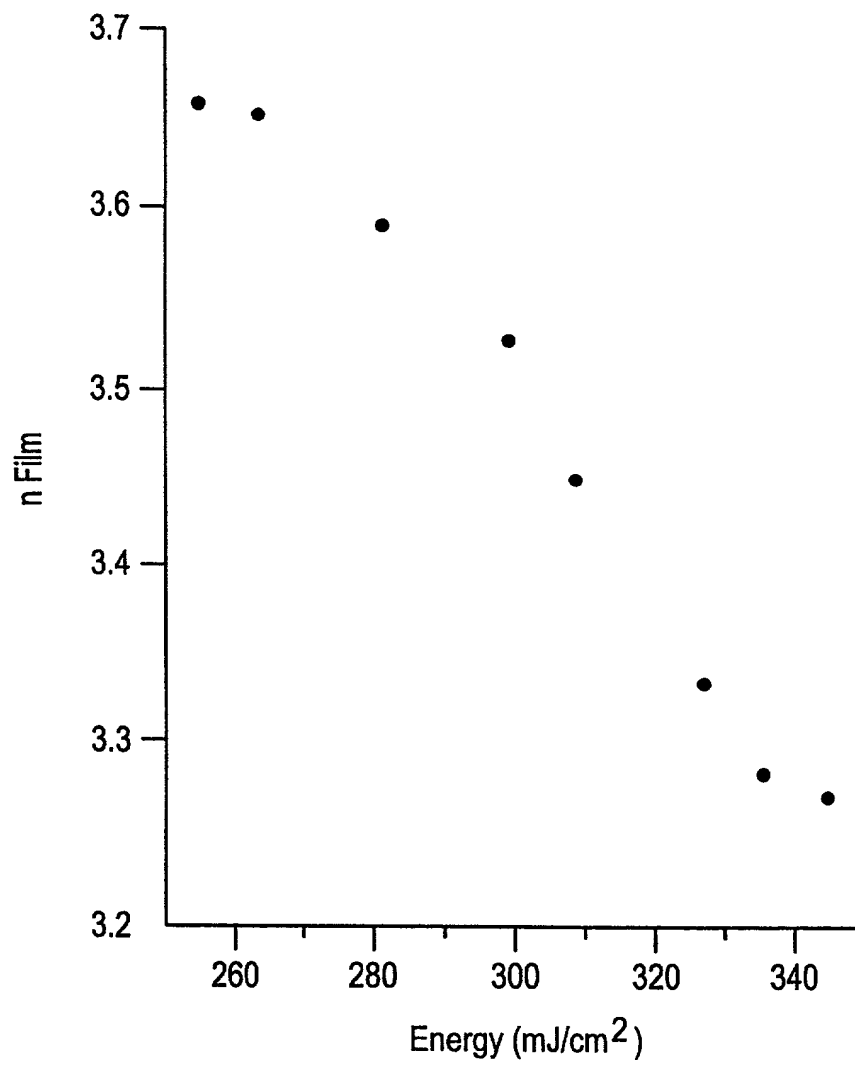


FIG. 4



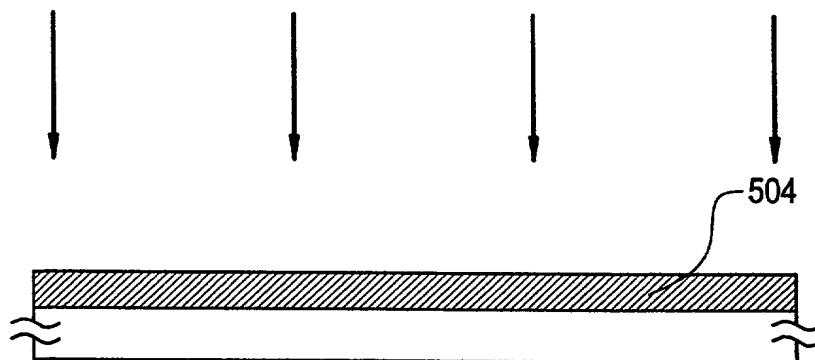


FIG. 5C

IMPURITY ION IMPLANTATION AND LASER LIGHT IRRADIATION

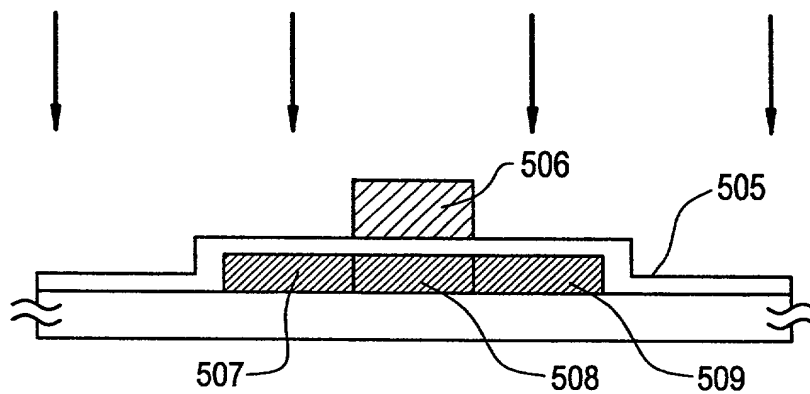


FIG. 5D

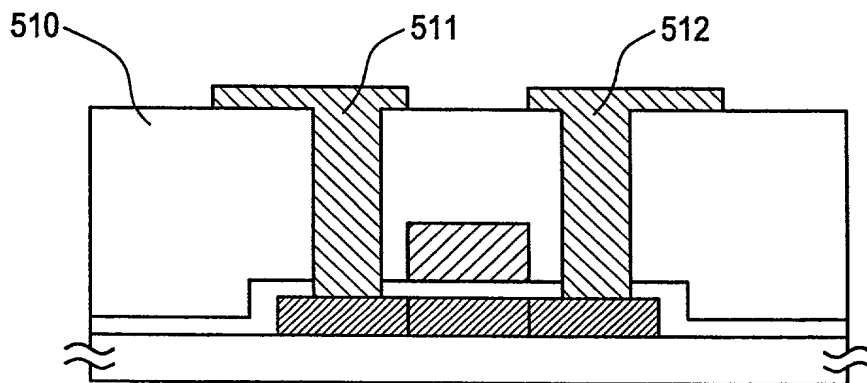


FIG. 6A

IRRADIATING LASER LIGHT TO ONE GLASS
SUBSTRATE FORMED ON CRYSTALLINE
SILICON FILM



FIG. 6B

MEASURING REFRACTIVE INDEX OF CRYSTALLINE
SILICON FILM TO WHICH LASER
LIGHT HAS BEEN IRRADIATED, BY ELLIPSOMETRY



FIG. 6C

INCREASING IRRADIATION ENERGY OF LASER
LIGHT, IN CASE THAT REFRACTIVE INDEX
OBTAINED BY THE FOREGOING IS LARGER
THAN PRESCRIBED REFRACTIVE INDEX



BACK TO FIG. 6A

FIG. 7A

IRRADIATING LASER LIGHT TO SOURCE/DRAIN
REGION OF THIN FILM TRANSISTOR FORMED ON
GLASS SUBSTRATE TO PERFORM ANNEALING



FIG. 7B

IRRADIATING LASER LIGHT TO CRYSTALLINE SILICON
FILM EVERY AFTER COMPLETING TREATMENT FOR
ONE SUBSTRATE, AND MEASURING REFRACTIVE
INDEX OF CRYSTALLINE SILICON FILM AFTER
IRRADIATION, BY ELLIPSOMETRY



FIG. 7C

INCREASING IRRADIATION ENERGY OF LASER
LIGHT IN CASE THAT THE FOREGOING REFRACTIVE
INDEX IS LARGER THAN PRESCRIBED VALUE, AND
DECREASING IRRADIATION ENERGY OF LASER
LIGHT IN CASE THAT THE FOREGOING REFRACTIVE
INDEX IS SMALLER THAN THE PRESCRIBED VALUE



BACK TO FIG. 7A